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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/554,086	10/21/2005	Shingo Hishiya	33082M287	2876
441 7590 11/05/2008 SMITH, GAMBRELL & RUSSELL 1130 CONNECTICUT AVENUE, N.W., SUITE 1130			EXAMINER	
			CHEN, BRET P	
WASHINGTON, DC 20036			ART UNIT	PAPER NUMBER
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			11/05/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Application No. Applicant(s) 10/554.086 HISHIYA, SHINGO Office Action Summary Examiner Art Unit Bret Chen 1792 -- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --Period for Reply A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS. WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION. Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b). Status 1) Responsive to communication(s) filed on 11 July 2008. 2a) This action is FINAL. 2b) This action is non-final. 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213. Disposition of Claims 4) Claim(s) 1-16 is/are pending in the application. 4a) Of the above claim(s) 9-16 is/are withdrawn from consideration. 5) Claim(s) _____ is/are allowed. 6) Claim(s) 1-8 is/are rejected. 7) Claim(s) _____ is/are objected to. 8) Claim(s) _____ are subject to restriction and/or election requirement. Application Papers 9) The specification is objected to by the Examiner. 10) ☐ The drawing(s) filed on 21 October 2005 is/are: a) ☐ accepted or b) ☐ objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152. Priority under 35 U.S.C. § 119 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)

2) Notice of Draftsperson's Patent Drawing Review (PTO-948)

Paper No(s)/Mail Date 10/21/05, 6/23/06, 8/25/06.

Interview Summary (PTO-413)
Paper No(s)/Mail Date.

6) Other:

Notice of Informal Patent Application

DETAILED ACTION

Claims 1-16 are pending in this application.

Election/Restrictions

Applicant's election of claims 1-8 in the reply filed on 7/11/08 is acknowledged. Because applicant did not distinctly and specifically point out the supposed errors in the restriction requirement, the election has been treated as an election without traverse (MPEP § 818.03(a)).

Claims 9-16 have been withdrawn from consideration as being directed to a nonelected invention.

Specification

Applicant is reminded of the proper language and format for an abstract of the disclosure.

The abstract should be in narrative form and generally limited to a single paragraph on a separate sheet within the range of 50 to 150 words. It is important that the abstract not exceed 150 words in length since the space provided for the abstract on the computer tape used by the printer is limited. The form and legal phrascology often used in patent claims, such as "means" and "said," should be avoided. The abstract should describe the disclosure sufficiently to assist readers in deciding whether there is a need for consulting the full patent text for details.

The language should be clear and concise and should not repeat information given in the title. It should avoid using phrases which can be implied, such as, "The disclosure concerns," "The disclosure defined by this invention," "The disclosure describes," etc.

It is noted that the abstract begins with "The present invention relates to". The examiner suggests its deletion.

Application/Control Number: 10/554,086

Art Unit: 1792

The title of the invention is not descriptive. A new title is required that is clearly indicative of the invention to which the claims are directed.

It is noted that the claimed invention is directed solely to a method. The examiner suggests amending the title to reflect same.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claims 7 is rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention

In claim 7 line 3, the term "low dielectric" is a relative term which renders the claim indefinite. The term "low" is not defined by the claim, the specification does not provide a standard for ascertaining the requisite degree, and one of ordinary skill in the art would not be reasonably apprised of the scope of the invention.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made. Application/Control Number: 10/554,086

Art Unit: 1792

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1-7 are rejected under 35 U.S.C. 103(a) as being unpatentable over Inoue (5,976,966) in view of Murakami et al. (2003/0087042). Inoue discloses a method of forming an insulating film by CVD on the surface of a semiconductor substrate formed with circuit elements such as transistors, and thereafter forming a hydrogen silsesquioxane resin film on the insulating film by spin-coating or the like followed by heat treatment steps (col.2 lines 30-52). This resin film is sequentially subjected to low temperature annealing at 400°C or lower and then to high temperature annealing at 700°C or higher (col.4 lines 6-28). It is specifically noted that the low temperature annealing changes the resin film into a silicon oxide film, and the high temperature annealing is performed in order to make dense the film quality of the silicon oxide film (col.2 line 53 - col.3 line 7). It is the examiner's position that this meets the limitation of modifying a surface. The high temperature annealing is performed by rapid thermal annealing in an oxidizing atmosphere of water vapor or the like (col.4 lines 22-28). However, the reference fails to teach applying a solution to form the interlayer insulating film.

Murakami discloses of forming a porous silicon oxide film for use as an interlayer insulating film by preparing an organic silane solution containing an organic silane, water and an alcohol, subjecting the organic silane to acid hydrolysis or alkali hydrolysis and then heat-treating the resulting reaction system in the presence of a surfactant to thus form the film (0011). It should be noted that an alternative method for forming the porous silicon oxide film is to use

Application/Control Number: 10/554,086

Art Unit: 1792

CVD or sputtering (0014). It is noted that Murakami fairly teaches the conventionality of forming a porous silicon oxide film by using an organic silane solution of by CVD. It would have been obvious to utilize the organic solution for the CVD process in Inoue with the expectation of obtaining similar results.

In claim 2, the applicant requires a specific oxidizing gas. It is noted that Inoue teaches an oxidizing atmosphere of water vapor.

In claims 3-4, the applicant requires a specific temperature range. It is noted that this feature is taught as indicated above.

In claims 5-7, the applicant requires a specific surface energy, surface contact angle, and dielectric constant, respectively. While it is noted that the feature is not explicitly taught by the references above, this limitation is inherently met because the references teach the claimed method steps.

Claim 8 is rejected under 35 U.S.C. 103(a) as being unpatentable over Inoue (5,976,966) in view of Murakami et al. (2003/0087042) and further in view of JP 52-111385.

The combination of Inoue and Murakami fail to teach the use of a polysiloxane to form the interlayer insulating film. JP' 385 teaches the conventionality of using a depositing a polysiloxane solution and heating in an oxidizing atmosphere to form a silicon oxide film (abstract). It would have been obvious to utilize the polysiloxane solution in the process of Inoue and Murakami with the expectation of obtaining similar results in the absence of a showing of unexpected results.

Art Unit: 1792

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Bret Chen whose telephone number is (571)272-1417. The examiner can normally be reached on 7:30am - 4:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy Meeks can be reached on (571) 272-1423. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/Bret Chen/ Primary Examiner, Art Unit 1792 11/2/08